



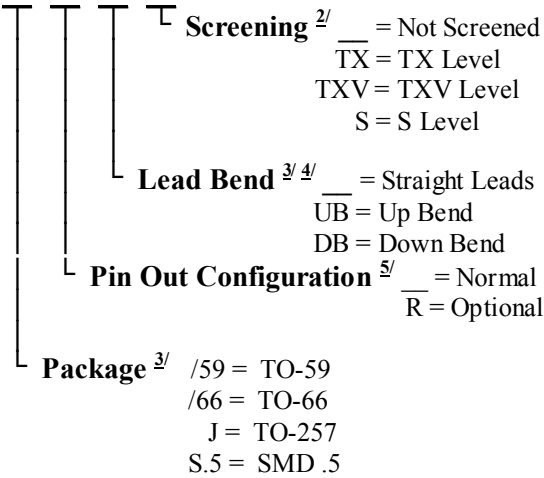
Solid State Devices, Inc.

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DESIGNER'S DATA SHEET

Part Number / Ordering Information ^{1/}

SFT5001



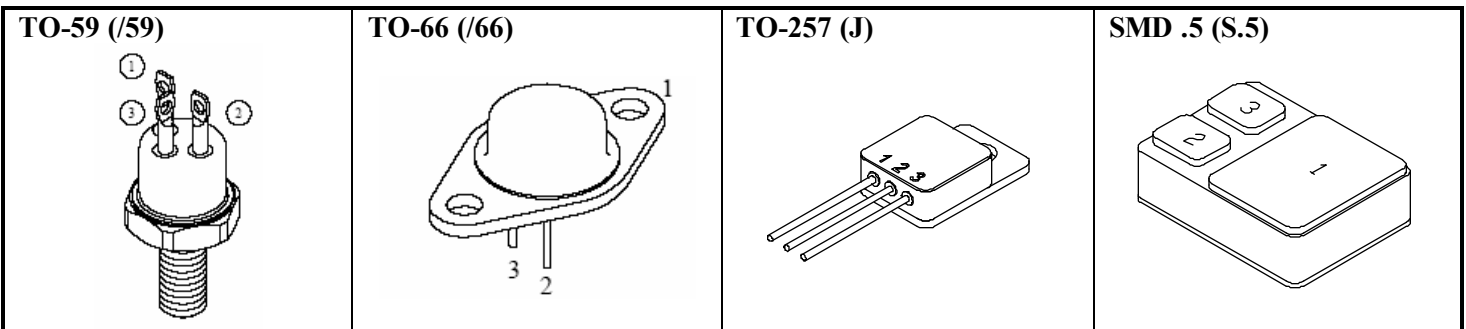
SFT5001

**5 AMPS
 125 Volts
 High Speed
 PNP Transistor**

Features:

- Radiation Tolerant
- Superior to JEDEC 2N5001 Series
- High Frequency, $f_T > 80\text{MHz}$
- Very Low Saturation
- Fast Switching, 130 ns Max $t(\text{on})$
- Designed for Complementary Use with SFT3997
- TX, TXV, S-Level Screening Available. Consult Factory.

Maximum Ratings	Symbol	Value	Units
Collector – Emitter Voltage	V_{CEO}	80	Volts
Collector – Base Voltage	V_{CBO}	125	Volts
Emitter – Base Voltage	V_{EBO}	7	Volts
Collector Current	I_{C}	5	Amps
Base Current	I_{B}	1	Amps
Total Power Dissipation @ $T_{\text{C}} = 100^{\circ}\text{C}$ Derate Above 100°C	P_{D}	30 0.3	Watts W/ $^{\circ}\text{C}$
Operating & Storage Temperature	$T_{\text{J}} \& T_{\text{STG}}$	-65 to +200	$^{\circ}\text{C}$
Maximum Thermal Resistance (Junction to Case)	$R_{\theta\text{JC}}$	3.33	$^{\circ}\text{C}/\text{W}$



NOTE: All specifications are subject to change without notification.
 SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: TR0099A

DOC



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SFT5001

Electrical Characteristics		Symbol	Min	Max	Units	
Collector – Emitter Blocking Voltage *	(I _C = 10 mA)	BV _{CEO}	80	—	Volts	
Collector – Base Blocking Voltage	(I _C = 20 μA)	BV _{CBO}	125	—	Volts	
Emitter – Base Blocking Voltage	(I _E = 20 μA)	BV _{EBO}	7	—	Volts	
Collector Cutoff Current	(V _{CE} = 40 V)	I _{CEO}	—	10	μA	
Collector Cutoff Current	(V _{CB} = 100 V)	I _{CBO}	—	1.0	μA	
Emitter Cutoff Current	(V _{EB} = 6 V)	I _{EBO}	—	1.0	μA	
DC Current Gain *	(I _C = 50 mA, V _{CE} = 5 V) (I _C = 1.0 A, V _{CE} = 5 V) (I _C = 5.0 A, V _{CE} = 5 V)	h _{FE}	50 50 30	— — —		
Collector-Emitter Saturation Voltage *	(I _C = 1.0 A, I _B = 100 mA) (I _C = 5.0 A, I _B = 500 mA)	V _{CE(SAT)}	— —	0.5 1.0	Volts	
Base-Emitter Saturation Voltage *	(I _C = 1.0 A, I _B = 100 mA) (I _C = 5.0 A, I _B = 500 mA)	V _{BE(SAT)}	— —	0.9 1.2	Volts	
Current Gain – Bandwidth Product	V _{CE} = 5 V, I _C = 0.5 A, f = 10 MHz	f _T	80	—	MHz	
Output Capacitance	V _{CB} = 10 V, I _E = 0 A, f = 1.0 MHz	C _{ob}	—	75	pF	
Delay Time	(V _{CC} = 20 V, I _C = 1.0 A, V _{BE(off)} = 3.7 V, I _{B1} = I _{B2} = 100 mA, R _L = 20 Ω)	t _(on)	t _d	—	150	ns
Rise Time		t _r	—			
Storage Time		t _(off)	t _s	—	500	ns
Fall Time		t _f	—			

NOTES: * Pulse Test: Pulse Width = 300μsec, Duty Cycle = 2% <u>1/</u> For Ordering Information, Price, and Availability Contact Factory. <u>2/</u> Screening per MIL-PRF-19500 <u>3/</u> For Package Outlines Contact Factory.	<u>4/</u> Up and Down Bend Configurations are Available for ‘J’ (TO-257) Packages Only. <u>5/</u> Optional Pin Out Configurations are Available for ‘J’ (TO-257) Packages Only. <u>6/</u> Unless Otherwise Specified, All Electrical Characteristics @25°C.
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Available Part Numbers:
 SFT5001/59 SFT5001/66 SFT5001J SFT5001JUB
 SFT5001JDB SFT5001JR SFT5001JRUB SFT5001JRDB
 SFT5001S.5

PIN ASSIGNMENT (Standard)			
Package	Collector	Emitter	Base
TO-59 (/59)	Pin 1	Pin 2	Pin 3
TO-66 (/66)	Case	Pin 2	Pin 3
TO-257 (J)	Pin 1	Pin 2	Pin 3
SMD .5 (S.5)	Pin 1	Pin 2	Pin 3
PIN ASSIGNMENT (Optional)			
Package	Collector	Emitter	Base
TO-257 (JR)	Pin 2	Pin 3	Pin 1